

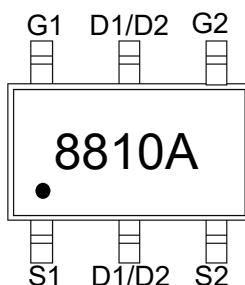


Features

- High power and current handing capability
- Lead free product is acquired
- Surface mount package
- ESD protected

Application

- Battery protection
- Load switch
- Power management

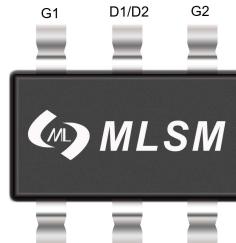


8810A: Device code

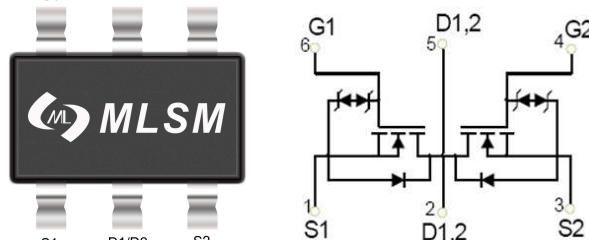
Marking and pin assignment

Product Summary

V _{DS}	R _{DS(ON)} MAX	I _D MAX
20V	15.5mΩ@10V	7A
	16.6mΩ@4.5V	



SOT-23-6L top view



Schematic diagram



Halogen-Free

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
Common Ratings (TC=25°C Unless Otherwise Noted)			
V _{DS}	Drain-Source Breakdown Voltage	20	V
V _{GS}	Gate-Source Voltage	±12	V
T _J	Maximum Junction Temperature	150	°C
T _{STG}	Storage Temperature Range	-55 to 150	°C
I _S	Diode Continuous Forward Current	Tc=25°C 7	A
Mounted on Large Heat Sink			
I _{DM}	Pulse Drain Current Tested	Tc=25°C 30	A
I _D	Continuous Drain Current	Tc=25°C 7	A
P _D	Maximum Power Dissipation	Tc=25°C 1.25	W
R _{θJA}	Thermal Resistance Junction-Ambient	100	°C/W

Ordering Information (Example)

Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MLSL8810A	SOT-23-6L	8810A	3,000	45,000	180,000	7"reel



Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
BV _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	20	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =20V, V _{GS} =0V	--	--	1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±10V, V _{DS} =0V	--	--	±5.0	μA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	0.4	0.75	1.0	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =10V, I _D =3A	--	12.0	15.5	mΩ
		V _{GS} =4.5V, I _D =3A	--	12.8	16.6	mΩ
		V _{GS} =3.8V, I _D =3A	--	13.0	17.0	mΩ
		V _{GS} =2.5V, I _D =3A	--	15.0	19.5	mΩ
		V _{GS} =1.8V, I _D =3A	--	21.5	35.0	mΩ
Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =10V, V _{GS} =0V, f=1MHz	--	783	--	pF
C _{OSS}	Output Capacitance		--	140	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	100	--	pF
Switching Characteristics						
Q _g	Total Gate Charge	V _{DS} =10V, I _D =7A, V _{GS} =4.5V	--	7.7	--	nC
Q _{gs}	Gate Source Charge		--	1.2	--	nC
Q _{gd}	Gate Drain Charge		--	2.4	--	nC
t _{d(on)}	Turn-on Delay Time	V _{DD} =10V, R _L =1.35Ω, V _{GS} =4.5V, R _G =3Ω	--	8.8	--	nS
t _r	Turn-on Rise Time		--	2.2	--	nS
t _{d(off)}	Turn-Off Delay Time		--	65	--	nS
t _f	Turn-Off Fall Time		--	26	--	nS
Source-Drain Diode Characteristics						
V _{SD}	Forward on voltage	T _J =25°C, I _S =7A	--	--	1.2	V

Typical Operating Characteristics

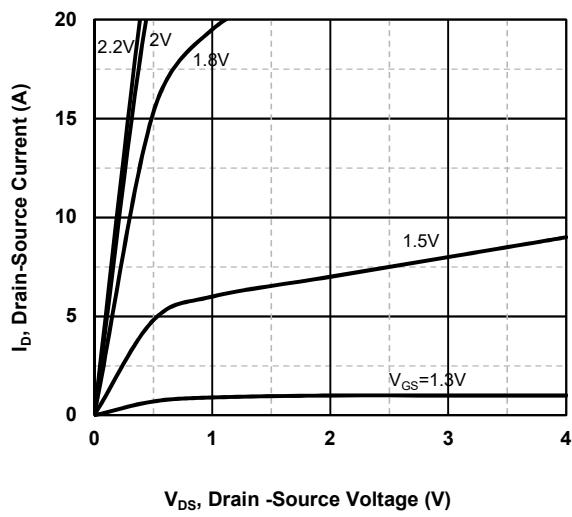


Fig1. Typical Output Characteristics

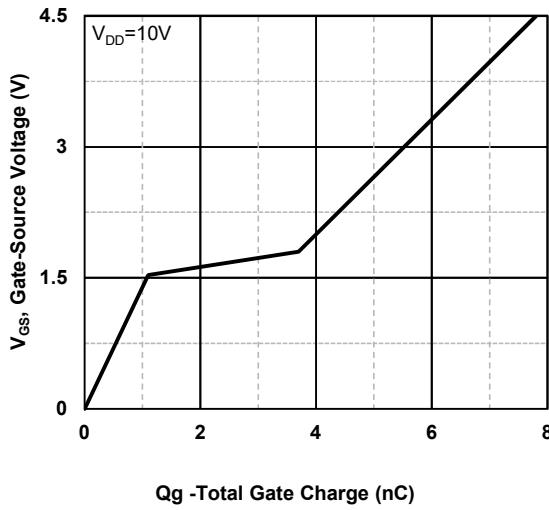


Fig2. Typical Gate Charge Vs. Gate-Source Voltage

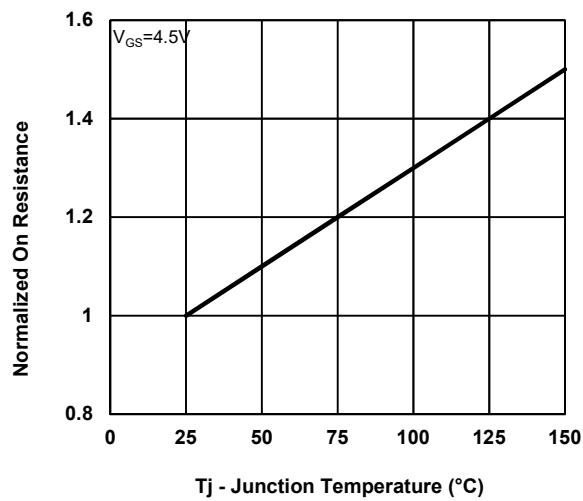


Fig3. Normalized On-Resistance Vs. Temperature

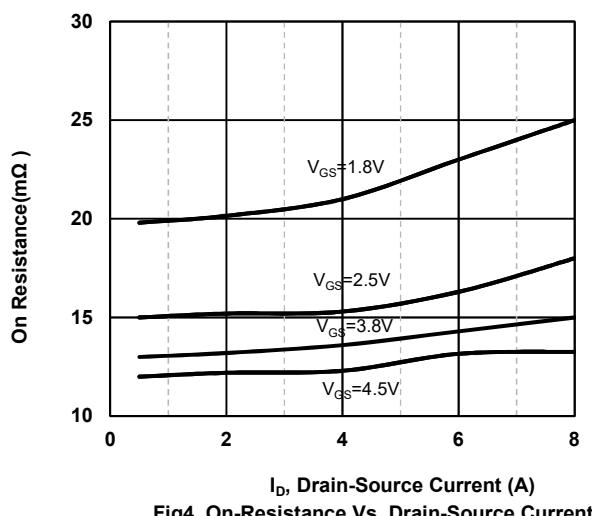


Fig4. On-Resistance Vs. Drain-Source Current

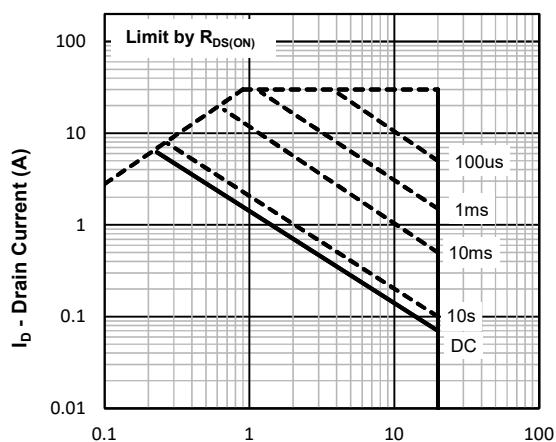


Fig5. Maximum Safe Operating Area

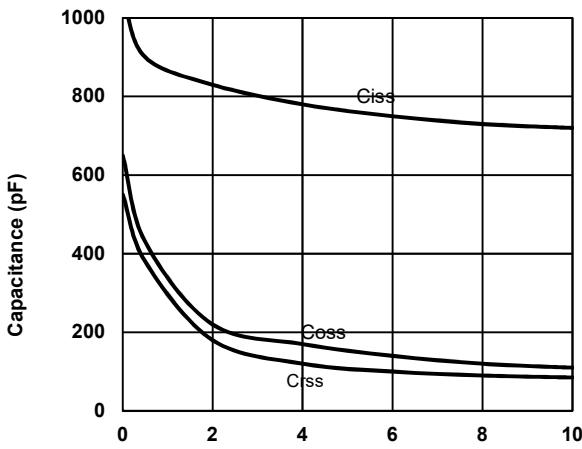
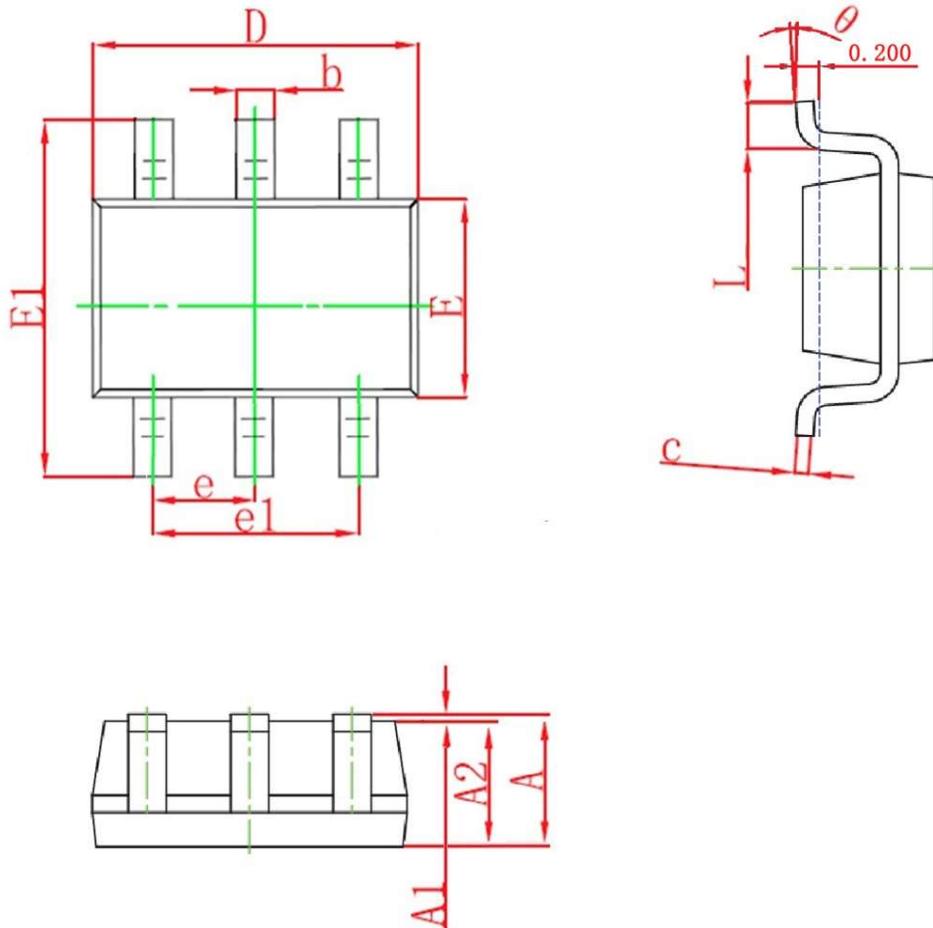


Fig6. Typical Capacitance Vs. Drain-Source Voltage



SOT-23-6L Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.000	1.200	0.039	0.047
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.600	3.000	0.102	0.118
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
K	0°	8°	0°	8°